

Schottky Barrier Diode

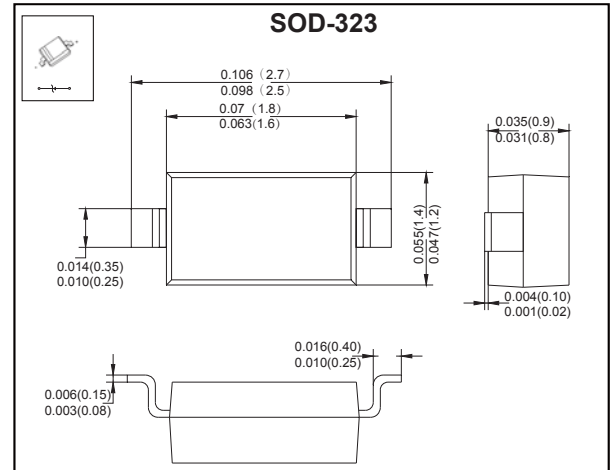
VOLTAGE RANGE: 30V PEAK PULSE POWER: 250mW

FEATURES

- Low Forward Voltage Drop
- Guard Ring Die Construction for Transient
- Protection Ideal for Low Logic Level Applications
- Low Capacitance
- Also Available in Lead Free Version

MECHANICAL DATA

- Case: SOD-323 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

Parameter	Symbol	Limit	Unit
Non-repetitive peak reverse voltage	VRM	30	V
Forward current	IFM	100	mA
Non-repetitive Peak Forward Surge Current @t = 8 .3ms	IFSM	2	A
Power dissipation TC=25°C	Ptot	250	mW
Thermal resistance junction to ambient	TeJA	400	°C/W
Junction temperature	TJ	125	°C
Storage temperature	TSTG	-55~+150	°C

Electrical Specification (TA=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage	VR	30			V	IR=100µA
Forward voltage	VF		300		mV	IF=2mA
			360			IF=15mA
			430	550		IF=50mA
			500	800		IF=100mA
Reverse current	IR			1	µA	VR=25V
Capacitance between terminals	CT		7		pF	VR=10V, f=1MHz

MARKING: SG

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

